NSN 5961-01-216-7271

Unitized Semiconductor Devices - Page 1 of 1

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Inclosure Material:

Metal

Overall Length:

0.185 inches

Terminal Length:

0.500 inches

Overall Diameter:

0.370 inches

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-99

Component Name And Quantity:

2 transistor

Mounting Method:

Terminal

Terminal Circle Diameter:

0.200 inches

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

15.0 collector to base voltage, dc all transistor and 8.0 collector to emitter voltage, dc all transistor and 4.8 emitter to base voltage, dc all transistor

Current Rating Per Characteristic:

1.00 nanoamperes source cutoff current all transistor

Power Rating Per Characteristic:

600.0 milliwatts small-signal input power, common-collector absolute all transistor

Transfer Ratio:

30.0 static forward current transfer ratio, common-emitter all transistor

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius junction

Special Features:

All transistor junction pattern arrangement: npn

Terminal Type And Quantity:

8 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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